PMEG6010ETR

High-temperature 60 V, 1 A Schottky barrier rectifier 10 October 2012 **Product data sheet**

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Average forward current: $I_{F(AV)} \le 1 A$
- Reverse voltage: V_R ≤ 60 V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T_i ≤ 175 °C

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _F	forward current	T _{sp} = 165 °C		-	-	1.4	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 140 °C; square wave	[1]	-	-	1	А
		δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave		-	-	1	Α
V_R	reverse voltage	T _j = 25 °C		-	-	60	V
V _F	forward voltage	I _F = 1 A; T _j = 25 °C		-	460	530	mV
I _R	reverse current	T_j = 25 °C; V_R = 60 V; $t_p \le$ 300 μs; $δ \le$ 0.02 ; pulsed		-	30	60	μA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$	-	4.4	-	ns
		T _j = 25 °C				

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	1 2	1 - 1 - 2
2	Α	anode	SOD123W	sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG6010ETR	SOD123W	plastic surface mounted package; 2 leads	SOD123W		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6010ETR	EK

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	60	V
I _F	forward current	T _{sp} = 165 °C		-	1.4	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 140 °C; square wave	[1]	-	1	Α
		δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave		-	1	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	680	mW
			[3]	-	1150	mW
			[1]	-	2140	mW
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

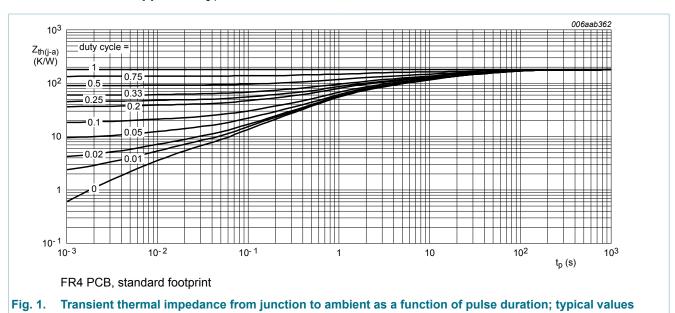
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]	-	-	220	K/W
		[1][3]	-	-	130	K/W	
	ambient	[1]	[1][4]	-	-	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	18	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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High-temperature 60 V, 1 A Schottky barrier rectifier

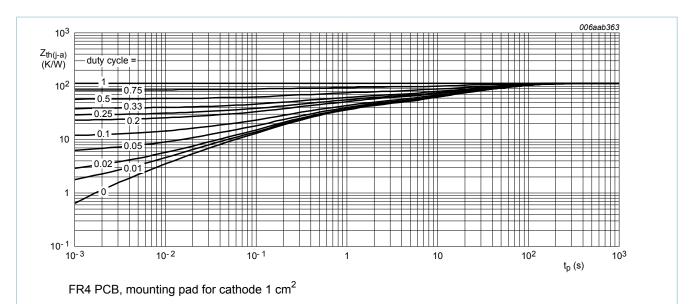
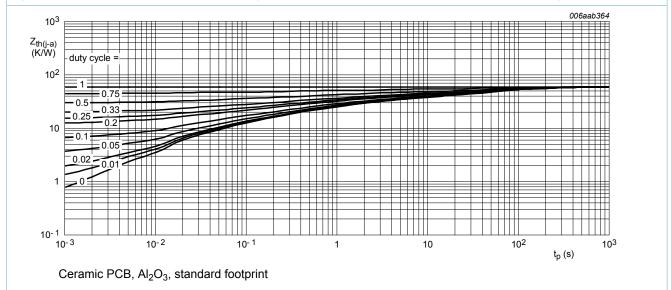


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. **Characteristics**

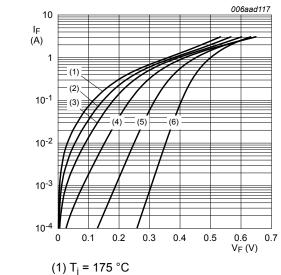
Characteristics Table 7.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage		I _F = 0.1 A; T _j = 25 °C	-	320	370	mV
		I _F = 0.7 A; T _j = 25 °C	-	430	490	mV
		I _F = 1 A; T _j = 25 °C	-	460	530	mV
		I _F = 1 A; T _j = -40 °C	-	510	590	mV
	I _F = 1 A; T _j = 125 °C	-	400	480	mV	
	I _F = 1 A; T _j = 150 °C	-	380	460	mV	

High-temperature 60 V, 1 A Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _F = 1 A; T _j = 175 °C	-	365	450	mV
I _R	reverse current	V_R = 5 V; T_j = 25 °C; t_p ≤ 300 μs; δ ≤ 0.02 ; pulsed	-	1.2	-	μA
		V_R = 10 V; T_j = 25 °C; t_p ≤ 300 μs; δ ≤ 0.02 ; pulsed	-	1.7	-	μA
	V_R = 60 V; T_j = 25 °C; t_p ≤ 300 μs; δ ≤ 0.02 ; pulsed	-	30	60	μA	
		V_R = 60 V; T_j = -40 °C; t_p ≤ 300 μs; δ ≤ 0.02 ; pulsed	-	0.6	10	μA
		V_R = 60 V; T_j = 125 °C; t_p ≤ 300 μs; δ ≤ 0.02 ; pulsed	-	14	50	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	120	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	40	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	4.4	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 40 \text{ A/}\mu\text{s}; T_j = 25 °C$	-	500	-	mV



(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

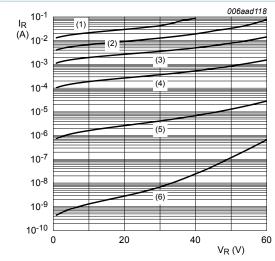
(3)
$$T_i = 125 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_j = 25 \, ^{\circ}C$$

(6)
$$T_j = -40 \, ^{\circ}C$$

Forward current as a function of forward Fig. 4. voltage; typical values



(1) $T_i = 175 \,^{\circ}C$

(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

(3)
$$T_i = 125 \, ^{\circ}C$$

(4)
$$T_i = 85 \,^{\circ}\text{C}$$

(5)
$$T_j = 25 \,^{\circ}C$$

(6)
$$T_j = -40 \, ^{\circ}C$$

Reverse current as a function of reverse Fig. 5. voltage; typical values

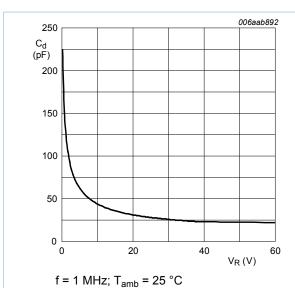
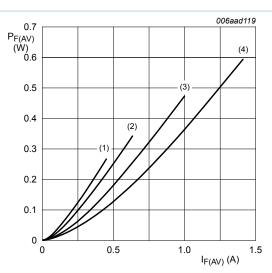


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



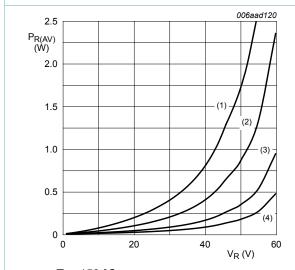
T_i = 175 °C $(1) \delta = 0.1$

 $(2) \delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_i = 150 °C

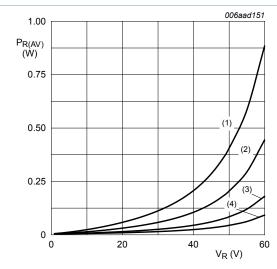
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$ $(4) \delta = 0.1$

Average reverse power dissipation as a

Fig. 8. function of reverse voltage; typical values



T_i = 125 °C

 $(1) \delta = 1$

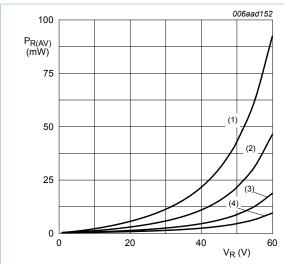
 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

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T_i = 85 °C

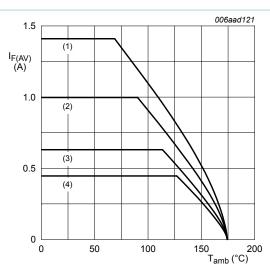
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 175 °C

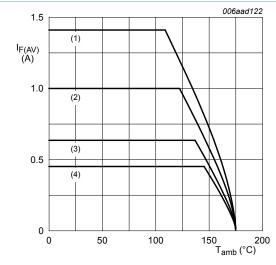
(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 175 °C

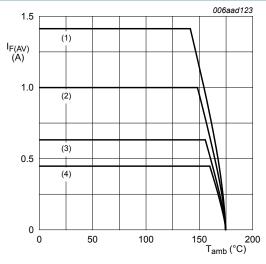
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 175 °C

 $(1) \delta = 1 (DC)$

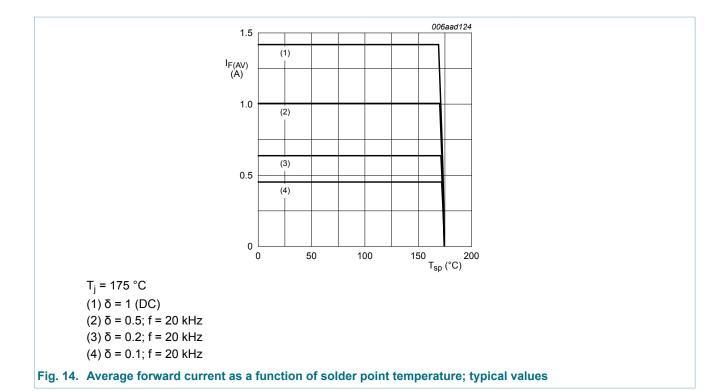
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

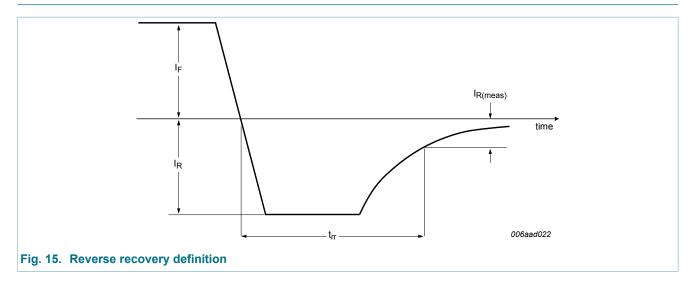
(4) δ = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of ambient temperature; typical values

High-temperature 60 V, 1 A Schottky barrier rectifier

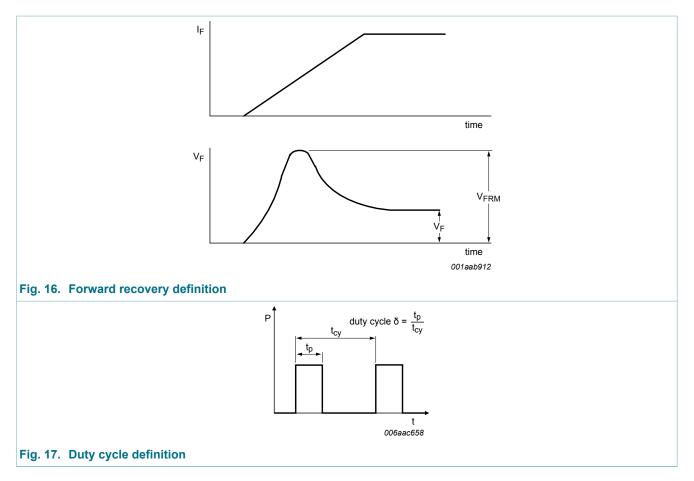


8. Test information



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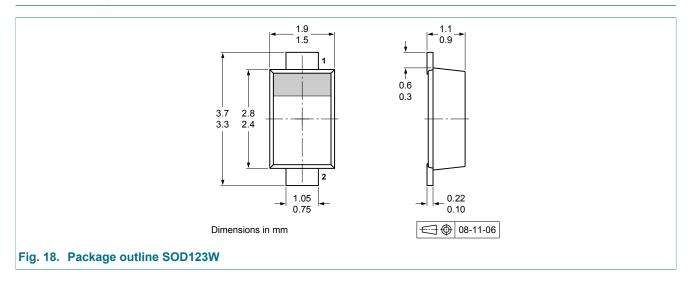
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

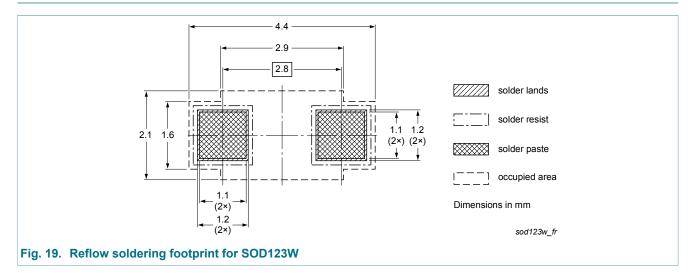
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline



10. Soldering



11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6010ETR v.1	20121010	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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